

1. Material Substrate GaAlAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)

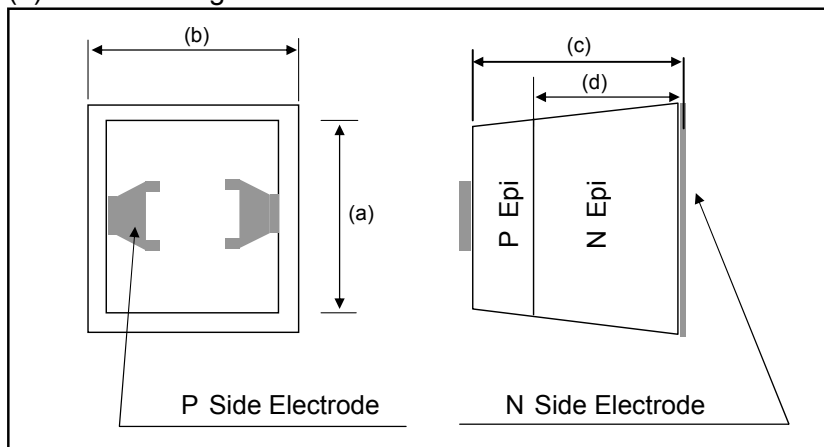
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.45	1.6	V	IF=50mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	5	7		mW	IF=50mA
Wavelength	λ_P		870		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		15		ns	
Fall Time	T_f		6.3		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

- 4. Mechanical Data**
- (a) Emission Area ----- 18.7mil x 18.7mil
 - (b) Bottom Area ----- 19.7mil x 19.7mil
 - (c) Bonding Pad ----- double pad
 - (d) Chip Thickness ----- 7mil
 - (e) Junction Height ----- 6.4mil



AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea

Tel. +82 63 839 1111 Fax. +82 63 835 8259

www.auk.co.kr

